



### **General Description**

The WSF07N10 is the highest performance trench N-ch MOSFET with extreme high cell density, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The WSF07N10 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

#### **Features**

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent Cdv/dt effect decline
- Green Device Available

### **Product Summery**

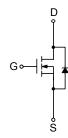
BVDSS	RDSON	ID		
100V	195mΩ	7A		

### **Applications**

- High Frequency Point-of-Load Synchronous Buck Converter
- Networking DC-DC Power System
- Load Switch

## **TO-252 Pin Configuration**





## **Absolute Maximum Ratings**

Symbol	Parameter	Rating	Units	
$V_{DS}$	Drain-Source Voltage	100	V	
$V_{GS}$	Gate-Source Voltage	±20	V	
I <sub>D</sub> @T <sub>C</sub> =25℃	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup>	Α		
I <sub>D</sub> @T <sub>C</sub> =100°C	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup>	4	Α	
I <sub>DM</sub>	Pulsed Drain Current <sup>2</sup>	21	Α	
P <sub>D</sub> @T <sub>A</sub> =25℃	Total Power Dissipation <sup>3</sup>	1.25	W	
T <sub>STG</sub>	Storage Temperature Range -55 to 170		$^{\circ}$	
T <sub>J</sub>	Operating Junction Temperature Range	-55 to 170	$^{\circ}$	

### **Thermal Data**

Symbol	Parameter	Тур.	Max.	Unit
R <sub>0JA</sub>	Thermal Resistance Junction-ambient <sup>1</sup>		70	°C/W
$R_{ heta JC}$	Thermal Resistance Junction-Case <sup>1</sup>		2.5	°C/W



# Electrical Characteristics (T<sub>J</sub>=25 C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V , I <sub>D</sub> =250uA	100			V
$\triangle BV_{DSS}/\triangle T_{J}$	BVDSS Temperature Coefficient	Reference to 25℃ , I <sub>D</sub> =1mA		0.098		V/°C
Б	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =10V , I <sub>D</sub> =1A		195	250	mΩ
R <sub>DS(ON)</sub>		V <sub>GS</sub> =6V , I <sub>D</sub> =1A		240	320	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	\\ -\\   -250\	1.5	2.0	3.0	V
$\triangle V_{GS(th)}$	V <sub>GS(th)</sub> Temperature Coefficient	$-V_{GS}=V_{DS}$ , $I_D=250uA$		-4.57		mV/℃
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =80V , V <sub>GS</sub> =0V , T <sub>J</sub> =25°C			1	
		V <sub>DS</sub> =80V , V <sub>GS</sub> =0V , T <sub>J</sub> =55°C			5	· uA
I <sub>GSS</sub>	Gate-Source Leakage Current	$V_{GS}$ = $\pm 20V$ , $V_{DS}$ = $0V$			±100	nA
gfs	Forward Transconductance	V <sub>DS</sub> =5V , I <sub>D</sub> =5A		1		S
$R_g$	Gate Resistance	V <sub>DS</sub> =0V , V <sub>GS</sub> =0V , f=1MHz		2	4	Ω
$Q_g$	Total Gate Charge (10V)	V <sub>DS</sub> =50V , V <sub>GS</sub> =10V , I <sub>D</sub> =1.3A		5.2		
$Q_gs$	Gate-Source Charge			0.75		nC
$Q_gd$	Gate-Drain Charge			1.4		
$T_{d(on)}$	Turn-On Delay Time			6		
T <sub>r</sub>	Rise Time	$V_{DD}$ =30V , $V_{GS}$ =10V , $R_{G}$ =6 $\Omega$		10		- ns
T <sub>d(off)</sub>	Turn-Off Delay Time	I <sub>D</sub> =1A , R <sub>L</sub> =30Ω		10		
T <sub>f</sub>	Fall Time			6		
Ciss	Input Capacitance	V <sub>DS</sub> =30V , V <sub>GS</sub> =0V , f=1MHz		320		
C <sub>oss</sub>	Output Capacitance			22		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			13		

### **Diode Characteristics**

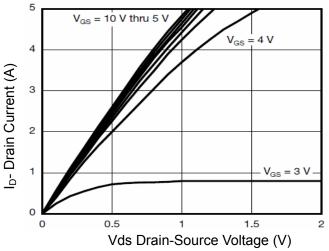
Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Is	Continuous Source Current <sup>1,6</sup>	V <sub>G</sub> =V <sub>D</sub> =0V , Force Current			3	Α
$V_{SD}$	Diode Forward Voltage <sup>2</sup>	V <sub>GS</sub> =0V , I <sub>S</sub> =3A , T <sub>J</sub> =25℃			1.2	V

### Notes:

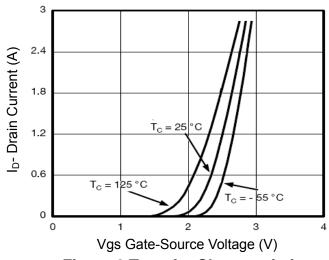
- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- **2.** Surface Mounted on FR4 Board,  $t \le 10$  sec.
- 3. Pulse Test: Pulse Width  $\leq$  300 $\mu$ s, Duty Cycle  $\leq$  2%.
- 4. Guaranteed by design, not subject to production



### **Typical Characteristics**



**Figure 1 Output Characteristics** 



**Figure 2 Transfer Characteristics** 

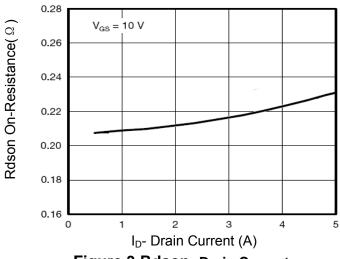


Figure 3 Rdson- Drain Current

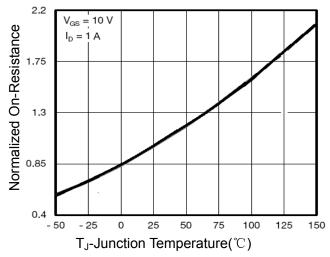


Figure 4 Rdson-JunctionTemperature

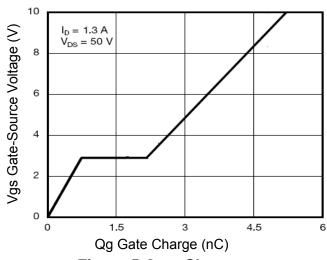


Figure 5 Gate Charge

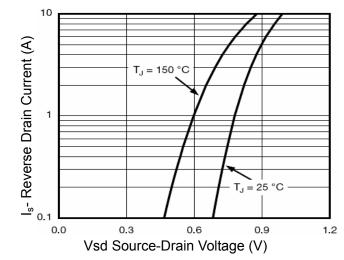


Figure 6 Source- Drain Diode Forward



## **Typical Characteristics**

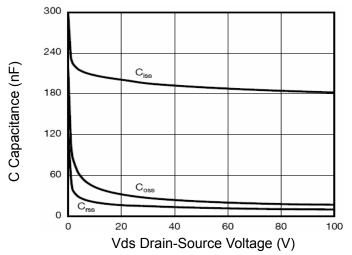


Figure 7 Capacitance vs Vds

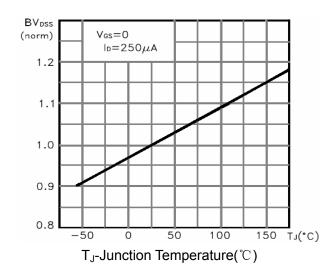
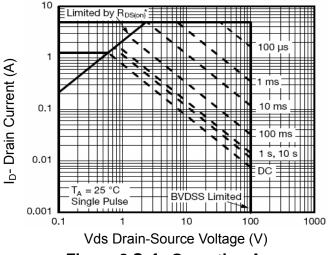


Figure 9 BV<sub>DSS</sub> vs Junction Temperature



**Figure 8 Safe Operation Area** 

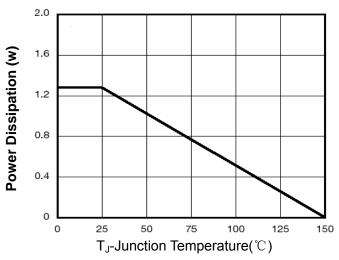
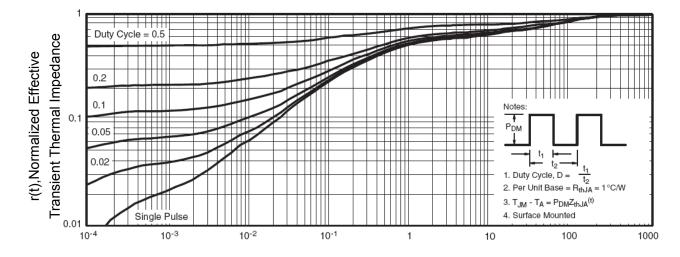


Figure 10 Power De-ratin



Square Wave Pluse Duration(sec)

Figure 11 Normalized Maximum Transient Thermal Impedance



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